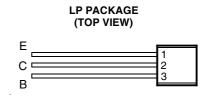
BOURNS®

- 20 W Pulsed Power Dissipation
- 100 V Capability
- 2 A Continuous Collector Current
- 4 A Peak Collector Current
- Customer-Specified Selections Available



MDTRAB

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	TIPP31		40		
Collector boso voltage (I _ 0)	TIPP31A	N	60	V	
Collector-base voltage ($I_E = 0$)	TIPP31B	^V сво	80		
	TIPP31C		100		
	TIPP31		40	v	
Collector-emitter voltage ($I_B = 0$)	TIPP31A	V _{CEO}	60		
	TIPP31B		80		
	TIPP31C		100		
Emitter-base voltage		V _{EBO}	5	V	
Continuous collector current		۱ _C	2	A	
Peak collector current (see Note 1)	I _{CM}	4	A		
Continuous base current	Ι _Β	1	A		
Continuous device dissipation at (or below) 25°C case temperature (see No	P _{tot}	0.8	W		
Pulsed power dissipation (see Note 3)	Ρ _T	20	W		
Operating junction temperature range	Тj	-55 to +150	°C		
Storage temperature range		T _{stg}	-55 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds	Τ _L	260	°C		

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 6.4 mW/°C.

3. $V_{CE} = 20$ V, $I_{C} = 1$ A, $t_{p} = 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

TIPP31, TIPP31A, TIPP31B, TIPP31C NPN SILICON POWER TRANSISTORS



electrical characteristics at 25°C case temperature

PARAMETER		TEST CONDITIONS			MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 5 mA (see Note 4)	I _B = 0	TIPP31 TIPP31A TIPP31B TIPP31C	40 60 80 100			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = 40 V$ $V_{CE} = 60 V$ $V_{CE} = 80 V$ $V_{CE} = 100 V$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIPP31 TIPP31A TIPP31B TIPP31C			0.2 0.2 0.2 0.2	mA
I _{CEO}	Collector cut-off current	$V_{CE} = 30 V$ $V_{CE} = 60 V$	I _B = 0 I _B = 0	TIPP31/31A TIPP31B/31C			0.3 0.3	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	l _C = 0				1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = 4 V$ $V_{CE} = 4 V$	$I_{\rm C} = 1 \text{ A}$ $I_{\rm C} = 2 \text{ A}$	(see Notes 4 and 5)	20 10			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = 375 mA	I _C = 2A	(see Notes 4 and 5)			1	V
V_{BE}	Base-emitter voltage	V _{CE} = 4 V	I _C = 2 A	(see Notes 4 and 5)			1.5	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.5 A	f = 1 kHz	20			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 0.5 A	f = 1 MHz	3			

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

BS

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

